

IN THE SPECIFICATION:

Page 80, lines 22-27 of the specification as originally filed, has been amended as follows:

An n-type semiconductor film 1109 is formed over a semiconductor film 1107. As an n-type impurity element, arsenic ~~[[Ar]]~~(As) or phosphorus (P) can be used. In the case of forming an n-type semiconductor film, an n-type (n+) silicon film can be formed by the glow discharge decomposition by plasma CVD using a mixed gas of SiH₄, H₂, and PH₃ (phosphine). Instead of the n-type semiconductor film 1109, a semiconductor film containing p-type impurity element such as boron (B) can be formed.